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What is "Embedded - Microcontrollers"?

"Embedded - Microcontrollers" refer to small, integrated circuits designed to perform specific tasks within larger systems. These microcontrollers are essentially compact computers on a single chip, containing a processor core, memory, and programmable input/output peripherals. They are called "embedded" because they are embedded within electronic devices to control various functions, rather than serving as standalone computers. Microcontrollers are crucial in modern electronics, providing the intelligence and control needed for a wide range of applications.

Applications of "<u>Embedded -</u> <u>Microcontrollers</u>"

Details

Product Status	Obsolete
Core Processor	RL78
Core Size	16-Bit
Speed	32MHz
Connectivity	CSI, I ² C, LINbus, UART/USART
Peripherals	DMA, LVD, POR, PWM, WDT
Number of I/O	21
Program Memory Size	16KB (16K x 8)
Program Memory Type	FLASH
EEPROM Size	4K x 8
RAM Size	2.5K x 8
Voltage - Supply (Vcc/Vdd)	1.6V ~ 5.5V
Data Converters	A/D 8x8/10b
Oscillator Type	Internal
Operating Temperature	-40°C ~ 85°C (TA)
Mounting Type	Surface Mount
Package / Case	30-LSSOP (0.240", 6.10mm Width)
Supplier Device Package	30-LSSOP
Purchase URL	https://www.e-xfl.com/product-detail/renesas-electronics-america/r5f104aaasp-v0

Email: info@E-XFL.COM

Address: Room A, 16/F, Full Win Commercial Centre, 573 Nathan Road, Mongkok, Hong Kong

(3/5)

Pin count	Package	Fields of Application Note	Ordering Part Number
48 pins	48-pin plastic LFQFP (7 × 7 mm, 0.5 mm pitch)	A	R5F104GAAFB#V0, R5F104GCAFB#V0, R5F104GDAFB#V0, R5F104GEAFB#V0, R5F104GFAFB#V0, R5F104GGAFB#V0, R5F104GHAFB#V0, R5F104GJAFB#V0
			R5F104GAAFB#X0, R5F104GCAFB#X0, R5F104GDAFB#X0, R5F104GEAFB#X0, R5F104GFAFB#X0, R5F104GGAFB#X0, R5F104GHAFB#X0, R5F104GJAFB#X0
			R5F104GKAFB#30, R5F104GLAFB#30
			R5F104GKAFB#50, R5F104GLAFB#50
		D	R5F104GADFB#V0, R5F104GCDFB#V0, R5F104GDDFB#V0, R5F104GEDFB#V0, R5F104GFDFB#V0, R5F104GGDFB#V0, R5F104GHDFB#V0, R5F104GJDFB#V0
			R5F104GADFB#X0, R5F104GCDFB#X0, R5F104GDDFB#X0, R5F104GEDFB#X0, R5F104GFDFB#X0, R5F104GGDFB#X0, R5F104GHDFB#X0, R5F104GJDFB#X0
		G	R5F104GAGFB#V0, R5F104GCGFB#V0, R5F104GDGFB#V0, R5F104GEGFB#V0, R5F104GFGFB#V0, R5F104GGGFB#V0, R5F104GHGFB#V0, R5F104GJGFB#V0
			R5F104GAGFB#X0, R5F104GCGFB#X0, R5F104GDGFB#X0, R5F104GEGFB#X0, R5F104GFGFB#X0, R5F104GGGFB#X0, R5F104GHGFB#X0, R5F104GJGFB#X0
			R5F104GKGFB#30, R5F104GLGFB#30
			R5F104GKGFB#50, R5F104GLGFB#50
	48-pin plastic HWQFN	A	R5F104GAANA#U0, R5F104GCANA#U0, R5F104GDANA#U0, R5F104GEANA#U0,
	$(7 \times 7 \text{ mm}, 0.5 \text{ mm pitch})$		R5F104GFANA#U0, R5F104GGANA#U0, R5F104GHANA#U0, R5F104GJANA#U0
			R5F104GAANA#W0, R5F104GCANA#W0, R5F104GDANA#W0, R5F104GEANA#W0, R5F104GFANA#W0, R5F104GGANA#W0, R5F104GHANA#W0, R5F104GJANA#W0
			R5F104GKANA#U0, R5F104GLANA#U0
			R5F104GKANA#W0, R5F104GLANA#W0
		D	R5F104GADNA#U0, R5F104GCDNA#U0, R5F104GDDNA#U0, R5F104GEDNA#U0,
			R5F104GFDNA#U0, R5F104GGDNA#U0, R5F104GHDNA#U0, R5F104GJDNA#U0
			R5F104GADNA#W0, R5F104GCDNA#W0, R5F104GDDNA#W0, R5F104GEDNA#W0, R5F104GFDNA#W0, R5F104GGDNA#W0, R5F104GHDNA#W0, R5F104GJDNA#W0
		G	R5F104GAGNA#U0, R5F104GCGNA#U0, R5F104GDGNA#U0, R5F104GEGNA#U0,
			R5F104GFGNA#U0, R5F104GGGNA#U0, R5F104GHGNA#U0, R5F104GJGNA#U0
			R5F104GAGNA#W0, R5F104GCGNA#W0, R5F104GDGNA#W0, R5F104GEGNA#W0, R5F104GFGNA#W0, R5F104GGGNA#W0, R5F104GHGNA#W0, R5F104GH
			R5F104GKGNA#U0, R5F104GLGNA#U0
			R5F104GKGNA#W0, R5F104GLGNA#W0
52 pins	52-pin plastic LQFP	A	R5F104JCAFA#V0, R5F104JDAFA#V0, R5F104JEAFA#V0, R5F104JFAFA#V0,
	$(10 \times 10 \text{ mm}, 0.65 \text{ mm pitch})$		R5F104JGAFA#V0, R5F104JHAFA#V0, R5F104JJAFA#V0
			R5F104JCAFA#X0, R5F104JDAFA#X0, R5F104JEAFA#X0, R5F104JFAFA#X0,
		D	R5F104JGAFA#X0, R5F104JHAFA#X0, R5F104JJAFA#X0 R5F104JCDFA#V0, R5F104JDDFA#V0, R5F104JEDFA#V0, R5F104JFDFA#V0,
		D	R5F104JGDFA#V0, R5F104JHDFA#V0, R5F104JJDFA#V0, R5F104JGDFA#V0
			R5F104JCDFA#X0, R5F104JDDFA#X0, R5F104JEDFA#X0, R5F104JFDFA#X0,
			R5F104JGDFA#X0, R5F104JHDFA#X0, R5F104JJDFA#X0
		G	R5F104JCGFA#V0, R5F104JDGFA#V0, R5F104JEGFA#V0, R5F104JFGFA#V0,
			R5F104JGGFA#V0, R5F104JHGFA#V0, R5F104JJGFA#V0
			R5F104JCGFA#X0, R5F104JDGFA#X0, R5F104JEGFA#X0, R5F104JFGFA#X0,
			R5F104JGGFA#X0, R5F104JHGFA#X0, R5F104JJGFA#X0

Note

For the fields of application, refer to Figure 1 - 1 Part Number, Memory Size, and Package of RL78/G14.

Caution The ordering part numbers represent the numbers at the time of publication. For the latest ordering part numbers, refer to the target product page of the Renesas Electronics website.

[44-pin, 48-pin, 52-pin, 64-pin products (code flash memory 96 KB to 256 KB)]

Caution This outline describes the functions at the time when Peripheral I/O redirection register 0, 1 (PIOR0, 1) are set to 00H.

	(PIORU, I) are set to				(1/2					
		44-pin	48-pin	52-pin	64-pin					
	Item	R5F104Fx	R5F104Gx	R5F104Jx	R5F104Lx					
		(x = F to H, J)	(x = F to H, J)	(x = F to H, J)	(x = F to H, J)					
Code flash me	emory (KB)	96 to 256	96 to 256	96 to 256	96 to 256					
Data flash me	emory (KB)	8	8	8	8					
RAM (KB)		12 to 24 Note	12 to 24 Note	12 to 24 Note	12 to 24 Note					
Address space	e	1 MB								
Main system clock	High-speed system clock	X1 (crystal/ceramic) oscillation, external main system clock input (EXCLK) HS (high-speed main) mode: 1 to 20 MHz (VDD = 2.7 to 5.5 V), HS (high-speed main) mode: 1 to 16 MHz (VDD = 2.4 to 5.5 V), LS (low-speed main) mode: 1 to 8 MHz (VDD = 1.8 to 5.5 V), LV (low-voltage main) mode: 1 to 4 MHz (VDD = 1.6 to 5.5 V)								
	High-speed on-chip oscillator clock (fiH)	HS (high-speed main) mode: 1 to 32 MHz (VDD = 2.7 to 5.5 V), HS (high-speed main) mode: 1 to 16 MHz (VDD = 2.4 to 5.5 V), LS (low-speed main) mode: 1 to 8 MHz (VDD = 1.8 to 5.5 V), LV (low-voltage main) mode: 1 to 4 MHz (VDD = 1.6 to 5.5 V)								
Subsystem clo	ock	XT1 (crystal) oscillation	n, external subsystem o	clock input (EXCLKS) 32	2.768 kHz					
Low-speed on	n-chip oscillator clock	15 kHz (TYP.): VDD = 1	.6 to 5.5 V							
General-purpo	ose register	8 bits \times 32 registers (8 bits \times 8 registers \times 4 banks)								
Minimum instr	ruction execution time	0.03125 μ s (High-speed on-chip oscillator clock: fi μ = 32 MHz operation)								
		0.05 μ s (High-speed system clock: f _{MX} = 20 MHz operation)								
		30.5 μs (Subsystem clock: fsuB = 32.768 kHz operation)								
Instruction set	ı	 Data transfer (8/16 bits) Adder and subtractor/logical operation (8/16 bits) Multiplication (8 bits × 8 bits, 16 bits × 16 bits), Division (16 bits ÷ 16 bits, 32 bits ÷ 32 bits) Multiplication and Accumulation (16 bits × 16 bits + 32 bits) Rotate, barrel shift, and bit manipulation (Set, reset, test, and Boolean operation), etc. 								
I/O port	Total	40	44	48	58					
	CMOS I/O	31	34	38	48					
	CMOS input	5	5	5	5					
	CMOS output	—	1	1	1					
	N-ch open-drain I/O (6 V tolerance)	4	4	4	4					
Timer	16-bit timer	8 channels (TAU: 4 channels, Time	er RJ: 1 channel, Timer	r RD: 2 channels, Timer	RG: 1 channel)					
	Watchdog timer	1 channel								
	Real-time clock (RTC)	1 channel								
		1 channel								
	12-bit interval timer	i channei	Timer outputs: 14 channels PWM outputs: 9 channels							
	12-bit interval timer Timer output	Timer outputs: 14 char								

(Note is listed on the next page.)

RENESAS

[80-pin, 100-pin products (code flash memory 384 KB to 512 KB)]

Caution This outline describes the functions at the time when Peripheral I/O redirection register 0, 1 (PIOR0, 1) are set to 00H.

			(1/2)					
		80-pin	100-pin					
	Item	R5F104Mx	R5F104Px					
		(x = K, L)	(x = K, L)					
Code flash me	emory (KB)	384 to 512	384 to 512					
Data flash me	mory (KB)	8	8					
RAM (KB)		32 to 48 Note	32 to 48 Note					
Address space	e	1 MB						
Main system clock	High-speed system clock	X1 (crystal/ceramic) oscillation, external main system clock input (EXCLK)HS (high-speed main) mode:1 to 20 MHz (VDD = 2.7 to 5.5 V),HS (high-speed main) mode:1 to 16 MHz (VDD = 2.4 to 5.5 V),LS (low-speed main) mode:1 to 8 MHz (VDD = 1.8 to 5.5 V),LV (low-voltage main) mode:1 to 4 MHz (VDD = 1.6 to 5.5 V)						
	High-speed on-chip oscillator clock (fiH)	HS (high-speed main) mode: 1 to 32 MHz (VDD = 2.7 to 5.5 V),						
Subsystem clo	ock	XT1 (crystal) oscillation, external subsystem cl	ock input (EXCLKS) 32.768 kHz					
Low-speed on	-chip oscillator clock	15 kHz (TYP.): VDD = 1.6 to 5.5 V						
General-purpo	ose register	8 bits \times 32 registers (8 bits \times 8 registers \times 4 bar	nks)					
Minimum instr	uction execution time	0.03125 μs (High-speed on-chip oscillator clock: fiн = 32 MHz operation)						
		0.05 μs (High-speed system clock: fмx = 20 MHz operation)						
		30.5 μs (Subsystem clock: fsuB = 32.768 kHz c	operation)					
Instruction set		 Data transfer (8/16 bits) Adder and subtractor/logical operation (8/16 I Multiplication (8 bits × 8 bits, 16 bits × 16 bits) Multiplication and Accumulation (16 bits × 16 Rotate, barrel shift, and bit manipulation (Set. 	, Division (16 bits ÷ 16 bits, 32 bits ÷ 32 bits) bits + 32 bits)					
I/O port	Total	74	92					
	CMOS I/O	64	82					
	CMOS input	5	5					
	CMOS output	1	1					
	N-ch open-drain I/O (6 V tolerance)	4	4					
Timer	16-bit timer	12 channels (TAU: 8 channels, Timer RJ: 1 channel, Timer RD: 2 channels, Timer RG: 1 channel)						
	Watchdog timer	1 channel						
	Real-time clock (RTC)	1 channel						
	12-bit interval timer	1 channel						
	Timer output	Timer outputs: 18 channels PWM outputs: 12 channels						
	RTC output	1 ● 1 Hz (subsystem clock: fs∪B = 32.768 kHz)						

Note

In the case of the 48 KB, this is about 47 KB when the self-programming function and data flash function are used (For details, see **CHAPTER 3** in the RL78/G14 User's Manual).

(1) Flash ROM: 16 to 64 KB of 30- to 64-pin products

(TA = -40 to +85°C	, 1.6 V \leq EVDD0 \leq	VDD \leq 5.5 V, Vss =	= EVsso = 0 V)(2/2)
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Parameter	Symbol			Conditions		MIN.	TYP.	MAX.	Unit
Supply current	IDD2	HALT mode	HS (high-speed main)	fносо = 64 MHz,	VDD = 5.0 V		0.80	3.09	mA
Note 1	Note 2		mode Note 7	fiH = 32 MHz Note 4	VDD = 3.0 V		0.80	3.09	1
				fносо = 32 MHz,	VDD = 5.0 V		0.49	2.40	1
				fiH = 32 MHz Note 4	VDD = 3.0 V		0.49	2.40	1
				fносо = 48 MHz,	VDD = 5.0 V		0.62	2.40	1
				fiH = 24 MHz Note 4	VDD = 3.0 V		0.62	2.40	1
				fносо = 24 MHz,	VDD = 5.0 V		0.4	1.83	
				fiн = 24 MHz Note 4	VDD = 3.0 V		0.4	1.83	1
				fносо = 16 MHz,	VDD = 5.0 V		0.37	1.38	1
				fiн = 16 MHz Note 4	VDD = 3.0 V		0.37	1.38	1
			LS (low-speed main)	fносо = 8 MHz,	VDD = 3.0 V		260	710	μΑ
			mode Note 7	fiH = 8 MHz Note 4	VDD = 2.0 V		260	710	1
			LV (low-voltage main)	fносо = 4 MHz,	VDD = 3.0 V		420	700	μΑ
			mode Note 7	fiH = 4 MHz Note 4	VDD = 2.0 V		420	700	
			HS (high-speed main)	fmx = 20 MHz Note 3,	Square wave input		0.28	1.55	mA
			mode Note 7	VDD = 5.0 V	Resonator connection		0.40	1.74	
				f _{MX} = 20 MHz ^{Note 3} ,	Square wave input		0.28	1.55	
			VDD = 3.0 V	Resonator connection		0.40	1.74		
			f _{MX} = 10 MHz Note 3,	Square wave input		0.19	0.86	1	
			VDD = 5.0 V	Resonator connection		0.25	0.93		
				f _{MX} = 10 MHz ^{Note 3} , V _{DD} = 3.0 V	Square wave input		0.19	0.86	
					Resonator connection		0.25	0.93	
			mode Note 7	f _{MX} = 8 MHz ^{Note 3} , V _{DD} = 3.0 V	Square wave input		95	550	μΑ
					Resonator connection		140	590	
				f _{MX} = 8 MHz Note 3,	Square wave input		95	550	
				VDD = 2.0 V	Resonator connection		140	590	
			Subsystem clock	fsue = 32.768 kHz Note 5,	Square wave input		0.25	0.57	μΑ
			operation	$T_A = -40^{\circ}C$	Resonator connection		0.44	0.76	
				fsue = 32.768 kHz ^{Note 5} ,	Square wave input		0.30	0.57	
				TA = +25°C	Resonator connection		0.49	0.76	
				fsue = 32.768 kHz Note 5,	Square wave input		0.36	1.17	
				TA = +50°C	Resonator connection		0.59	1.36	
				fsub = 32.768 kHz Note 5,	Square wave input		0.49	1.97	
				TA = +70°C	Resonator connection		0.72	2.16	
				fsub = 32.768 kHz Note 5,	Square wave input		0.97	3.37	
				TA = +85°C	Resonator connection		1.16	3.56	
	IDD3	STOP mode	TA = -40°C				0.18	0.51	μΑ
	Note 6	Note 8	TA = +25°C				0.24	0.51	μΛ -
			TA = +50°C				0.29	1.10	
			TA = +70°C				0.41	1.90	
			TA = +85°C				0.90	3.30	

(Notes and Remarks are listed on the next page.)



(4) Peripheral Functions (Common to all products)

(TA = -40 to +85°C, 1.6 V \leq EVDD0 = EVDD1 \leq VDD \leq 5.5 V, Vss = EVss0 = EVss1 = 0 V)

Parameter	Symbol	Condit	ions	MIN.	TYP.	MAX.	Unit
Low-speed on-chip oscilla- tor operating current	I _{FIL} Note 1				0.20		μA
RTC operating current	IRTC Notes 1, 2, 3				0.02		μA
12-bit interval timer operat- ing current	IIT Notes 1, 2, 4				0.02		μA
Watchdog timer operating current	I _{WDT} Notes 1, 2, 5	fı∟ = 15 kHz			0.22		μA
A/D converter operating cur- rent	IADC Notes 1, 6	When conversion at maximum speed	Normal mode, AV _{REFP} = V _{DD} = 5.0 V		1.3	1.7	mA
		Low voltage mode, AV _{REFP} = V _{DD} = 3.0 V		0.5	0.7	mA	
A/D converter reference voltage current	IADREF Note 1				75.0		μA
Temperature sensor operat- ing current	ITMPS Note 1				75.0		μA
D/A converter operating cur- rent	IDAC Notes 1, 11, 13	Per D/A converter channel			1.5	mA	
Comparator operating cur-	I _{CMP} Notes 1, 12, 13	VDD = 5.0 V,	Window mode		12.5		μA
rent		Regulator output voltage = 2.1 V	Comparator high-speed mode		6.5		μΑ
			Comparator low-speed mode		1.7		μΑ
		VDD = 5.0 V,	Window mode		8.0		μA
		Regulator output voltage = 1.8 V	Comparator high-speed mode		4.0		μΑ
			Comparator low-speed mode		1.3		μA
LVD operating current	ILVD Notes 1, 7				0.08		μΑ
Self-programming operat- ing current	IFSP Notes 1, 9				2.50	12.20	mA
BGO operating current	IBGO Notes 1, 8				2.50	12.20	mA
SNOOZE operating current	ISNOZ Note 1	ADC operation	The mode is performed Note 10		0.50	0.60	mA
			The A/D conversion opera- tions are performed, Low volt- age mode, AVREFP = VDD = 3.0 V		1.20	1.44	
	С	CSI/UART operation			0.70	0.84	
		DTC operation			3.10		

Note 1. Current flowing to VDD.

Note 2. When high speed on-chip oscillator and high-speed system clock are stopped.

Note 3. Current flowing only to the real-time clock (RTC) (excluding the operating current of the low-speed on-chip oscillator and the XT1 oscillator). The supply current of the RL78 microcontrollers is the sum of the values of either IDD1 or IDD2, and IRTC, when the real-time clock operates in operation mode or HALT mode. When the low-speed on-chip oscillator is selected, IFIL should be added. IDD2 subsystem clock operation includes the operational current of the real-time clock.

Note 4. Current flowing only to the 12-bit interval timer (excluding the operating current of the low-speed on-chip oscillator and the XT1 oscillator). The supply current of the RL78 microcontrollers is the sum of the values of either IDD1 or IDD2, and IIT, when the 12-bit interval timer operates in operation mode or HALT mode. When the low-speed on-chip oscillator is selected, IFIL should be added.

Remark 1. p: CSI number (p = 00, 01, 10, 11, 20, 21, 30, 31), m: Unit number (m = 0, 1),

n: Channel number (n = 0 to 3), g: PIM number (g = 0, 1, 3 to 5, 14)

Remark 2. fMCK: Serial array unit operation clock frequency (Operation clock to be set by the CKSmn bit of serial mode register mn (SMRmn). m: Unit number,

n: Channel number (mn = 00 to 03, 10 to 13))



Parameter	Symbol	Conditions	HS (high-speed r mode	main)	LS (low-speed n mode	nain)	LV (low-voltage r mode	main)	Unit
			MIN.	MAX.	MIN.	MAX.	MIN.	MAX.	
Data setup time (reception)	tsu: dat	$\begin{array}{l} 2.7 \ \text{V} \leq E V_{\text{DD0}} \leq 5.5 \ \text{V}, \\ \text{C}_{\text{b}} = 50 \ \text{pF}, \ \text{R}_{\text{b}} = 2.7 \ \text{k}\Omega \end{array}$	1/f _{MCK} + 85 Note 2		1/fмск + 145 Note 2		1/fmck + 145 Note 2		ns
		$\begin{array}{l} 1.8 \text{ V} \leq EV_{\text{DD0}} \leq 5.5 \text{ V}, \\ \text{Cb} = 100 \text{ pF}, \text{ Rb} = 3 \text{ k}\Omega \end{array}$	1/fмск + 145 Note 2		1/fмск + 145 Note 2		1/fmck + 145 Note 2		ns
		$\label{eq:linear} \begin{array}{l} 1.8 \mbox{ V} \leq EV_{\mbox{DD0}} < 2.7 \mbox{ V}, \\ C_b \mbox{ = 100 pF}, \mbox{ R}_b \mbox{ = 5 } \end{array}$	1/fмск + 230 Note 2		1/fмск + 230 Note 2		1/fMCK + 230 Note 2		ns
		$\label{eq:linear} \begin{array}{l} 1.7 \mbox{ V} \leq EV_{\mbox{DD0}} < 1.8 \mbox{ V}, \\ C_{\mbox{b}} = 100 \mbox{ pF}, \mbox{ R}_{\mbox{b}} = 5 k\Omega \end{array}$	1/fмск + 290 Note 2		1/fмск + 290 Note 2		1/fMCK + 290 Note 2		ns
		$\label{eq:linear} \begin{array}{l} 1.6 \mbox{ V} \leq EV_{DD0} < 1.8 \mbox{ V}, \\ C_b \mbox{ = 100 pF}, \mbox{ R}_b \mbox{ = 5 } \end{array}$	_		1/fмск + 290 Note 2		1/fMCK + 290 Note 2		ns
Data hold time (transmission)	thd: dat	$\begin{array}{l} 2.7 \ \text{V} \leq \text{EV}_{\text{DD0}} \leq 5.5 \ \text{V}, \\ \text{C}_{\text{b}} = 50 \ \text{pF}, \ \text{R}_{\text{b}} = 2.7 \ \text{k}\Omega \end{array}$	0	305	0	305	0	305	ns
		$\label{eq:linear} \begin{array}{l} 1.8 \mbox{ V} \leq EV_{DD0} \leq 5.5 \mbox{ V}, \\ C_b = 100 \mbox{ pF}, \mbox{ R}_b = 3 \mbox{ k}\Omega \end{array}$	0	355	0	355	0	355	ns
		$\label{eq:linear} \begin{array}{l} 1.8 \mbox{ V} \leq EV_{DD0} < 2.7 \mbox{ V}, \\ C_b = 100 \mbox{ pF}, \mbox{ R}_b = 5 \mbox{ k}\Omega \end{array}$	0	405	0	405	0	405	ns
		$\label{eq:linear} \begin{array}{l} 1.7 \mbox{ V} \leq EV_{DD0} < 1.8 \mbox{ V}, \\ C_b = 100 \mbox{ pF}, \mbox{ R}_b = 5 \mbox{ k}\Omega \end{array}$	0	405	0	405	0	405	ns
		$\label{eq:linear} \begin{array}{l} 1.6 \mbox{ V} \leq EV_{\mbox{DD0}} < 1.8 \mbox{ V}, \\ C_b \mbox{ = 100 pF, } R_b \mbox{ = 5 } k\Omega \end{array}$	_		0	405	0	405	ns

(5) During communication at same potential (simplified I²C mode)

(TA = -40 to +85°C, 1.6 V \leq EVDD0 = EVDD1 \leq VDD \leq 5.5 V, VSS = EVSS0 = EVSS1 = 0 V)

(2/2)

Note 1. The value must also be equal to or less than fMCK/4.

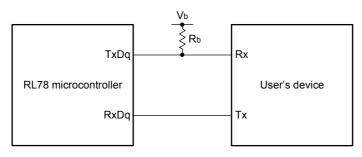
Note 2. Set the fMCK value to keep the hold time of SCLr = "L" and SCLr = "H".

Caution Select the normal input buffer and the N-ch open drain output (VDD tolerance (for the 30- to 52-pin products)/EVDD tolerance (for the 64- to 100-pin products)) mode for the SDAr pin and the normal output mode for the SCLr pin by using port input mode register g (PIMg) and port output mode register h (POMh).

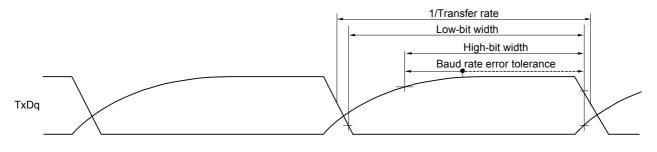
(**Remarks** are listed on the next page.)

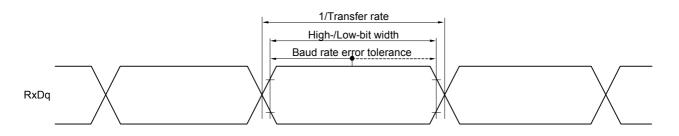


UART mode connection diagram (during communication at different potential)



UART mode bit width (during communication at different potential) (reference)





Remark 1. $Rb[\Omega]$: Communication line (TxDq) pull-up resistance,

Cb[F]: Communication line (TxDq) load capacitance, Vb[V]: Communication line voltage

Remark 2. q: UART number (q = 0 to 3), g: PIM and POM number (g = 0, 1, 5, 14)

Remark 3. fMCK: Serial array unit operation clock frequency

(Operation clock to be set by the CKSmn bit of serial mode register mn (SMRmn). m: Unit number, n: Channel number (mn = 00 to 03, 10 to 13))

Remark 4. UART2 cannot communicate at different potential when bit 1 (PIOR01) of peripheral I/O redirection register 0 (PIOR0) is 1.



(8) Communication at different potential (1.8 V, 2.5 V, 3 V) (CSI mode) (master mode, SCKp... internal clock output)

Parameter	Symbol	Conditions			HS (high-speed main) mode		d main)	LV (low-voltage main) mode		Unit
				MIN.	MAX.	MIN.	MAX.	MIN.	MAX.	
SCKp cycle time	t КСҮ1	tксү1 ≥ 4/fc∟к		300		1150		1150		ns
			$\begin{array}{l} 2.7 \ V \leq EV_{DD0} < 4.0 \ V, \\ 2.3 \ V \leq V_b \leq 2.7 \ V, \\ C_b = 30 \ pF, \ R_b = 2.7 \ k\Omega \end{array}$	500		1150		1150		ns
				1150		1150		1150		ns
SCKp high-level width	tкн1			tксү1/2 - 75		tксү1/2 - 75		tксү1/2 - 75		ns
		$\begin{split} & 2.7 \ V \leq EV_{DD0} < 4.0 \ V, \\ & 2.3 \ V \leq V_b \leq 2.7 \ V, \\ & C_b = 30 \ p\text{F}, \ R_b = 2.7 \ k\Omega \\ & 1.8 \ V \leq EV_{DD0} < 3.3 \ V, \\ & 1.6 \ V \leq V_b \leq 2.0 \ V \ Note, \\ & C_b = 30 \ p\text{F}, \ R_b = 5.5 \ k\Omega \end{split}$		tксү1/2 - 170		tксү1/2 - 170		tксү1/2 - 170		ns
				tксү1/2 - 458		tксү1/2 - 458		tксү1/2 - 458		ns
SCKp low-level width	tĸ∟1	$\begin{array}{l} 4.0 \ V \leq EV_{DD0} \leq 5.5 \ V, \\ 2.7 \ V \leq V_b \leq 4.0 \ V, \\ C_b = 30 \ pF, \ R_b = 1.4 \ k\Omega \end{array}$		tксү1/2 - 12		tксү1/2 - 50		tксү1/2 - 50		ns
		$2.3~V \leq V_b \leq 2$	$2.7 \text{ V} \le \text{EV}_{\text{DD0}} < 4.0 \text{ V},$ $2.3 \text{ V} \le V_b \le 2.7 \text{ V},$ $C_b = 30 \text{ pF}, \text{ R}_b = 2.7 \text{ k}\Omega$			tксү1/2 - 50		tксү1/2 - 50		ns
		$\begin{array}{l} 1.8 \ V \leq EV_{DD0} \\ 1.6 \ V \leq V_b \leq 2. \\ C_b = 30 \ pF, \ R_b \end{array}$	0 V ^{Note} ,	tксү1/2 - 50		tксү1/2 - 50		tксү1/2 - 50		ns

(TA = -40 to +85°C, 1.8 V \leq EVDD0 = EVDD1 \leq VDD \leq 5.5 V, VSS = EVSS0 = EVSS1 = 0 V)

Note Use it with $EVDD0 \ge Vb$.

(Remarks are listed two pages after the next page.)



Caution Select the TTL input buffer for the SIp pin and the N-ch open drain output (VDD tolerance (for the 30- to 52-pin products)/EVDD tolerance (for the 64- to 100-pin products)) mode for the SOp pin and SCKp pin by using port input mode register g (PIMg) and port output mode register g (POMg). For VIH and VIL, see the DC characteristics with TTL input buffer selected.

(2/3)

(8) Communication at different potential (1.8 V, 2.5 V, 3 V) (CSI mode) (master mode, SCKp... internal clock output)

Parameter	Symbol	Conditions		speed main) ode	LS (low-speed main) mode		LV (low-voltage main) mode		Unit
			MIN.	MAX.	MIN.	MAX.	MIN.	MAX.	
SIp setup time (to SCKp↑) ^{Note 1}	tsıĸı		81		479		479		ns
		$\begin{array}{l} 2.7 \ V \leq EV_{DD0} < 4.0 \ V, \\ 2.3 \ V \leq V_b \leq 2.7 \ V, \\ C_b = 30 \ pF, \ R_b = 2.7 \ k\Omega \end{array}$	177		479		479		ns
		$\begin{array}{l} 1.8 \ V \leq EV_{DD0} < 3.3 \ V, \\ 1.6 \ V \leq V_b \leq 2.0 \ V \ \text{Note 2}, \\ C_b = 30 \ pF, \ R_b = 5.5 \ k\Omega \end{array}$	479		479		479		ns
SIp hold time (from SCKp↑) ^{Note 1}	tksi1		19		19		19		ns
		$\begin{array}{l} 2.7 \ V \leq EV_{DD0} < 4.0 \ V, \\ 2.3 \ V \leq V_b \leq 2.7 \ V, \\ C_b = 30 \ pF, \ R_b = 2.7 \ k\Omega \end{array}$	19		19		19		ns
		$ \begin{split} & 1.8 \ V \leq EV_{DD0} < 3.3 \ V, \\ & 1.6 \ V \leq V_b \leq 2.0 \ V \ ^{Note \ 2}, \\ & C_b = 30 \ pF, \ R_b = 5.5 \ k\Omega \end{split} $	19		19		19		ns
Delay time from SCKp↓ to SOp output ^{Note 1}	tkso1			100		100		100	ns
		$\begin{array}{l} 2.7 \; V \leq EV_{DD0} < 4.0 \; V, \\ 2.3 \; V \leq V_b \leq 2.7 \; V, \\ C_b = 30 \; pF, \; R_b = 2.7 \; k\Omega \end{array}$		195		195		195	ns
		$ \begin{split} & 1.8 \ V \leq EV_{DD0} < 3.3 \ V, \\ & 1.6 \ V \leq V_b \leq 2.0 \ V \ ^{Note \ 2}, \\ & C_b = 30 \ pF, \ R_b = 5.5 \ k\Omega \end{split} $		483		483		483	ns

(TA = -40 to +85°C, 1.8 V \leq EVDD0 = EVDD1 \leq VDD \leq 5.5 V, Vss = EVss0 = EVss1 = 0 V)

Note 1. When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1.

Note 2. Use it with $EV_{DD0} \ge V_b$.

(Remarks are listed on the page after the next page.)



Caution Select the TTL input buffer for the SIp pin and the N-ch open drain output (VDD tolerance (for the 30- to 52-pin products)/EVDD tolerance (for the 64- to 100-pin products)) mode for the SOp pin and SCKp pin by using port input mode register g (PIMg) and port output mode register g (POMg). For VIH and VIL, see the DC characteristics with TTL input buffer selected.

(3/3)

(8) Communication at different potential (1.8 V, 2.5 V, 3 V) (CSI mode) (master mode, SCKp... internal clock output)

Parameter	Symbol	Conditions		peed main) ode	LS (low-speed main) mode		LV (low-voltage main) mode		Unit
			MIN.	MAX.	MIN.	MAX.	MIN.	MAX.	
SIp setup time (to SCKp↓) ^{Note 1}	tsıĸı		44		110		110		ns
		$\begin{array}{l} 2.7 \; V \leq EV_{DD0} < 4.0 \; V, \\ 2.3 \; V \leq V_b \leq 2.7 \; V, \\ C_b = 30 \; pF, \; R_b = 2.7 \; k\Omega \end{array}$	44		110		110		ns
		$ \begin{split} & 1.8 \ \text{V} \leq \text{EV}_{\text{DD0}} < 3.3 \ \text{V}, \\ & 1.6 \ \text{V} \leq \text{V}_{\text{b}} \leq 2.0 \ \text{V} \ \text{Note} \ ^2, \\ & \text{C}_{\text{b}} = 30 \ \text{pF}, \ \text{R}_{\text{b}} = 5.5 \ \text{k}\Omega \end{split} $	110		110		110		ns
SIp hold time (from SCKp↓) ^{Note 1}	tks⊓		19		19		19		ns
		$\begin{array}{l} 2.7 \ V \leq EV_{DD0} < 4.0 \ V, \\ 2.3 \ V \leq V_b \leq 2.7 \ V, \\ C_b = 30 \ pF, \ R_b = 2.7 \ k\Omega \end{array}$	19		19		19		ns
		$\label{eq:linear} \begin{array}{l} 1.8 \ V \leq EV_{DD0} < 3.3 \ V, \\ 1.6 \ V \leq V_b \leq 2.0 \ V \ ^{Note \ 2}, \\ C_b = 30 \ pF, \ R_b = 5.5 \ k\Omega \end{array}$	19		19		19		ns
Delay time from SCKp↑ to SOp output ^{Note 1}	tkso1			25		25		25	ns
		$\begin{array}{l} 2.7 \ V \leq EV_{DD0} < 4.0 \ V, \\ 2.3 \ V \leq V_b \leq 2.7 \ V, \\ C_b = 30 \ pF, \ R_b = 2.7 \ k\Omega \end{array}$		25		25		25	ns
		$ \begin{split} & 1.8 \ \text{V} \leq \text{EV}_{\text{DD0}} < 3.3 \ \text{V}, \\ & 1.6 \ \text{V} \leq \text{V}_{b} \leq 2.0 \ \text{V} \ ^{\text{Note 2}}, \\ & \text{C}_{b} = 30 \ \text{pF}, \ \text{R}_{b} = 5.5 \ \text{k}\Omega \end{split} $		25		25		25	ns

$(TA = -40 \text{ to } +85^{\circ}C, 1.8 \text{ V} \le \text{EVDD0} = \text{EVDD1} \le \text{VDD} \le 5.5 \text{ V}, \text{ Vss} = \text{EVss0} = \text{EVss1} = 0 \text{ V})$

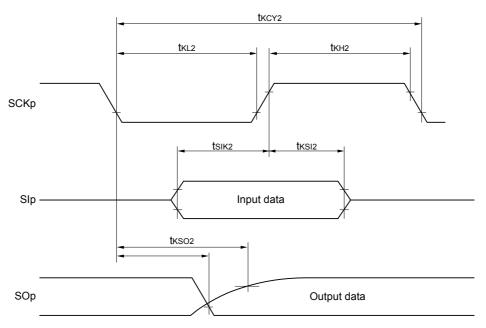
Note 1. When DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.

Note 2. Use it with $EV_{DD0} \ge V_b$.

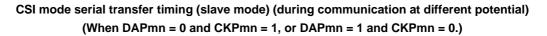
(**Remarks** are listed on the next page.)

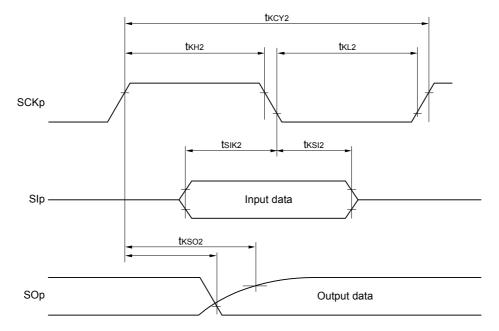


Caution Select the TTL input buffer for the SIp pin and the N-ch open drain output (VDD tolerance (for the 30- to 52-pin products)/EVDD tolerance (for the 64- to 100-pin products)) mode for the SOp pin and SCKp pin by using port input mode register g (PIMg) and port output mode register g (POMg). For VIH and VIL, see the DC characteristics with TTL input buffer selected.



CSI mode serial transfer timing (slave mode) (during communication at different potential) (When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1.)





- Remark 1. p: CSI number (p = 00, 01, 10, 20, 30, 31), m: Unit number (m = 0, 1), n: Channel number (n = 0 to 3), g: PIM and POM number (g = 0, 1, 3 to 5, 14)
- Remark 2. CSI01 of 48-, 52-, 64-pin products, and CSI11 and CSI21 cannot communicate at different potential. Use other CSI for communication at different potential.
 Also, communication at different potential cannot be performed during clock synchronous serial communication with the slave select function.

2.5.2 Serial interface IICA

(1) I²C standard mode

```
(TA = -40 to +85°C, 1.6 V \leq EVDD0 = EVDD1 \leq VDD \leq 5.5 V, VSS = EVSS0 = EVSS1 = 0 V)
```

Parameter	Symbol	Conditions			peed main) ode	LS (low-speed main) mode		LV (low-voltage main) mode		Unit
				MIN.	MAX.	MIN.	MAX.	MIN.	MAX.	
SCLA0 clock	fscl	Standard mode:	$2.7~V \leq EV_{\text{DD0}} \leq 5.5~V$	0	100	0	100	0	100	kHz
frequency		fc∟κ ≥ 1 MHz	$1.8 \text{ V} \leq EV_{\text{DD0}} \leq 5.5 \text{ V}$	0	100	0	100	0	100	kHz
			$1.7~V \leq EV_{\text{DD0}} \leq 5.5~V$	0	100	0	100	0	100	kHz
			$1.6~V \leq EV_{\text{DD0}} \leq 5.5~V$	-	_	0	100	0	100	kHz
Setup time of	tsu: sta	$2.7 \text{ V} \leq \text{EV}_{\text{DD0}} \leq 8$	5.5 V	4.7		4.7		4.7		μs
restart condition		$1.8 \text{ V} \le \text{EV}_{\text{DD0}} \le 5.5 \text{ V}$		4.7		4.7		4.7		μs
		$1.7 \text{ V} \leq \text{EV}_{\text{DD0}} \leq 5.5 \text{ V}$		4.7		4.7		4.7		μs
		$1.6 \text{ V} \leq \text{EV}_{\text{DD0}} \leq 8$	5.5 V	-	_	4.7		4.7		μs
Hold time Note 1	thd: STA	$2.7 \text{ V} \leq \text{EV}_{\text{DD0}} \leq 5.5 \text{ V}$		4.0		4.0		4.0		μs
		$1.8 \text{ V} \leq \text{EV}_{\text{DD0}} \leq 8$	$1.8 \text{ V} \leq \text{EV}_{\text{DD0}} \leq 5.5 \text{ V}$			4.0		4.0		μs
		$1.7 \text{ V} \leq \text{EV}_{\text{DD0}} \leq 5.5 \text{ V}$		4.0		4.0		4.0		μs
		$1.6 \text{ V} \leq \text{EV}_{\text{DD0}} \leq 8$	5.5 V	-	_	4.0		4.0		μs
Hold time when	t∟ow	$2.7 \text{ V} \leq \text{EV}_{\text{DD0}} \leq 8$	5.5 V	4.7		4.7		4.7		μs
SCLA0 = "L"		$1.8 \text{ V} \leq \text{EV}_{\text{DD0}} \leq 8$	5.5 V	4.7		4.7		4.7		μs
		$1.7 \text{ V} \leq \text{EV}_{\text{DD0}} \leq 8$	5.5 V	4.7		4.7		4.7		μs
		$1.6 \text{ V} \leq \text{EV}_{\text{DD0}} \leq 8$	5.5 V	-	_	4.7		4.7		μs
Hold time when	tніgн	$2.7 V \leq EV_{DD0} \leq 8$	5.5 V	4.0		4.0		4.0		μs
SCLA0 = "H"		$1.8 \text{ V} \leq \text{EV}_{\text{DD0}} \leq 8$	5.5 V	4.0		4.0		4.0		μs
		$1.7 \text{ V} \leq \text{EV}_{\text{DD0}} \leq 3$	5.5 V	4.0		4.0		4.0		μs
		$1.6 \text{ V} \leq \text{EV}_{\text{DD0}} \leq 8$	5.5 V		- 	4.0		4.0		μs

 $(\ensuremath{\textit{Notes}}, \ensuremath{\textit{Caution}}, \ensuremath{\text{and}} \ensuremath{\textit{Remark}}$ are listed on the next page.)



(2) I²C fast mode

(TA = -40 to +85°C, 1.6 V \leq EVDD0 = EVDD1 \leq VDD \leq 5.5 V, VSS = EVSS0 = EVSS1 = 0 V)

Parameter	Symbol	nbol Conditions		· · ·	h-speed mode	LS (low-speed main) mode		LV (low-voltage main) mode		Unit
				MIN.	MIN. MAX.		MAX.	MIN.	MAX.	
SCLA0 clock frequency	fscL	Fast mode:	$2.7~V \leq EV_{DD0} \leq 5.5~V$	0	400	0	400	0	400	kHz
		fc∟k ≥ 3.5 MHz	$1.8~V \leq EV_{\text{DD0}} \leq 5.5~V$	0	400	0	400	0	400	kHz
Setup time of restart condi-	tsu: sta	$2.7~V \leq EV_{DD0} \leq$	5.5 V	0.6		0.6		0.6		μs
tion		$1.8 \text{ V} \leq \text{EV}_{\text{DD0}} \leq$	5.5 V	0.6		0.6		0.6		μs
Hold time Note 1	thd: STA	$2.7~V \leq EV_{DD0} \leq$	$2.7 \text{ V} \leq \text{EV}_{\text{DD0}} \leq 5.5 \text{ V}$			0.6		0.6		μs
		$1.8 \text{ V} \leq \text{EV}_{\text{DD0}} \leq 5.5 \text{ V}$		0.6		0.6		0.6		μs
Hold time when SCLA0 = "L"	tLow $2.7 \text{ V} \leq \text{EV}_{\text{DD0}} \leq$		5.5 V	1.3		1.3		1.3		μs
		$1.8 \text{ V} \leq \text{EV}_{\text{DD0}} \leq$	5.5 V	1.3		1.3		1.3		μs
Hold time when SCLA0 = "H"	tнigн	$2.7~V \leq EV_{DD0} \leq$	5.5 V	0.6		0.6		0.6		μs
		$1.8 \text{ V} \leq \text{EV}_{\text{DD0}} \leq$	5.5 V	0.6		0.6		0.6		μs
Data setup time (reception)	tsu: dat	$2.7~V \leq EV_{DD0} \leq$	5.5 V	100		100		100		ns
		$1.8 \text{ V} \leq EV_{DD0} \leq$	5.5 V	100		100		100		ns
Data hold time (transmission)	thd: dat	$2.7 \text{ V} \leq EV_{DD0} \leq$	5.5 V	0	0.9	0	0.9	0	0.9	μs
Note 2		$1.8 \text{ V} \leq EV_{DD0} \leq$	5.5 V	0	0.9	0	0.9	0	0.9	μs
Setup time of stop condition	tsu: sto	$2.7 \text{ V} \leq EV_{DD0} \leq$	5.5 V	0.6		0.6		0.6		μs
		$1.8 \text{ V} \leq \text{EV}_{\text{DD0}} \leq$	5.5 V	0.6		0.6		0.6		μs
Bus-free time	t BUF	$2.7 \text{ V} \leq EV_{DD0} \leq$	5.5 V	1.3		1.3		1.3		μs
		$1.8 \text{ V} \leq \text{EV}_{\text{DD0}} \leq$	5.5 V	1.3		1.3		1.3		μs

Note 1. The first clock pulse is generated after this period when the start/restart condition is detected.

Note 2. The maximum value (MAX.) of the DEAT is during normal transfer and a wait state is inserted in the ACK (acknowledge) timing.

- Caution The values in the above table are applied even when bit 2 (PIOR02) in the peripheral I/O redirection register 0 (PIOR0) is 1. At this time, the pin characteristics (IOH1, IOL1, VOH1, VOL1) must satisfy the values in the redirect destination.
- **Remark** The maximum value of C_b (communication line capacitance) and the value of R_b (communication line pull-up resistor) at that time in each mode are as follows.

Fast mode: C_b = 320 pF, R_b = 1.1 k Ω



3. ELECTRICAL SPECIFICATIONS (G: INDUSTRIAL APPLICATIONS TA = -40 to +105°C)

This chapter describes the following electrical specifications. Target products G: Industrial applications $T_A = -40$ to $+105^{\circ}C$ R5F104xxGxx

- Caution 1. The RL78 microcontrollers have an on-chip debug function, which is provided for development and evaluation. Do not use the on-chip debug function in products designated for mass production, because the guaranteed number of rewritable times of the flash memory may be exceeded when this function is used, and product reliability therefore cannot be guaranteed. Renesas Electronics is not liable for problems occurring when the on-chip debug function is used.
- Caution 2. With products not provided with an EVDD0, EVDD1, EVSS0, or EVSS1 pin, replace EVDD0 and EVDD1 with VDD, or replace EVSS0 and EVSS1 with VSS.
- Caution 3. The pins mounted depend on the product. Refer to 2.1 Port Functions to 2.2.1 Functions for each product in the RL78/G14 User's Manual.
- Caution 4. Please contact Renesas Electronics sales office for derating of operation under TA = +85 to +105°C. Derating is the systematic reduction of load for the sake of improved reliability.
- Remark When RL78/G14 is used in the range of T_A = -40 to +85°C, see 2. ELECTRICAL SPECIFICATIONS (T_A = -40 to +85°C).



$TA = -40 \text{ to } +105^{\circ}\text{C}, 2.4 \text{ V} \le \text{EVDD0} = \text{EVDD1} \le \text{VDD} \le 5.5 \text{ V}, \text{VSS} = \text{EVSS0} = \text{EVSS1} = 0 \text{ V} $ (2)								
Items	Symbol	Conditions		MIN.	TYP.	MAX.	Unit	
Output current, low ^{Note 1}	IOL1	Per pin for P00 to P06, P10 to P17, P30, P31, P40 to P47, P50 to P57, P64 to P67, P70 to P77, P80 to P87, P100 to P102, P110, P111, P120, P130, P140 to P147				8.5 Note 2	mA	
		Per pin for P60 to P63				15.0 Note 2	mA	
		Total of P00 to P04, P40 to P47,	$4.0~V \leq EV_{DD0} \leq 5.5~V$			40.0	mA	
		P102, P120, P130, P140 to P145	$2.7 \text{ V} \le \text{EV}_{\text{DD0}} < 4.0 \text{ V}$			15.0	mA	
		(When duty \leq 70% ^{Note 3})	$2.4 \text{ V} \le \text{EV}_{\text{DD0}} < 2.7 \text{ V}$			9.0	mA	
		Total of P05, P06, P10 to P17,	$4.0~V \leq EV_{DD0} \leq 5.5~V$			40.0	mA	
			$2.7 \text{ V} \leq \text{EV}_{\text{DD0}} < 4.0 \text{ V}$			35.0	mA	
		P60 to P67, P70 to P77, P80 to P87, P100, P101, P110, P111, P146, P147 (When duty ≤ 70% ^{Note 3})	2.4 V ≤ EVDD0 < 2.7 V			20.0	mA	
		Total of all pins (When duty \leq 70% ^{Note 3})				80.0	mA	
lo	IOL2	Per pin for P20 to P27, P150 to P156				0.4 Note 2	mA	
		Total of all pins (When duty \leq 70% ^{Note 3})	$2.4 \text{ V} \leq \text{VDD} \leq 5.5 \text{ V}$			5.0	mA	

(TA = -40 to +105°C, 2.4 V \leq EVDD0 = EVDD1 \leq VDD \leq 5.5 V, VSS = EVSS0 = EVSS1 = 0 V)

(2/5)

Note 1. Value of current at which the device operation is guaranteed even if the current flows from an output pin to the EVsso, EVss1, and Vss pins.

Note 2. Do not exceed the total current value.

Note 3. Specification under conditions where the duty factor \leq 70%.

The output current value that has changed to the duty factor > 70% the duty ratio can be calculated with the following expression (when changing the duty factor from 70% to n%).

- Total output current of pins = (IoL × 0.7)/(n × 0.01)
 - <Example> Where n = 80% and IoL = 10.0 mA

Total output current of pins = $(10.0 \times 0.7)/(80 \times 0.01) \approx 8.7$ mA

However, the current that is allowed to flow into one pin does not vary depending on the duty factor.

A current higher than the absolute maximum rating must not flow into one pin.

Remark Unless specified otherwise, the characteristics of alternate-function pins are the same as those of the port pins.



(6) Communication at different potential (1.8 V, 2.5 V, 3 V) (CSI mode) (master mode, SCKp... internal clock output)

Parameter	Symbol	Conditions	HS (high-spe	Unit	
			MIN.	MAX.	
SIp setup time (to SCKp↑) ^{Note}	tsiкı		162		ns
		$\begin{array}{l} 2.7 \ V \leq EV_{DD0} < 4.0 \ V, \\ 2.3 \ V \leq V_b \leq 2.7 \ V, \\ C_b = 30 \ pF, \ R_b = 2.7 \ k\Omega \end{array}$	354		ns
		$\label{eq:VDD0} \begin{array}{l} 2.4 \ V \leq EV_{DD0} < 3.3 \ V, \\ 1.6 \ V \leq V_b \leq 2.0 \ V, \\ C_b = 30 \ pF, \ R_b = 5.5 \ k\Omega \end{array}$	958		ns
SIp hold time (from SCKp↑) ^{Note}	tksi1		38		ns
		$\label{eq:VDD0} \begin{split} & 2.7 \; V \leq EV_{DD0} < 4.0 \; V, \\ & 2.3 \; V \leq V_{b} \leq 2.7 \; V, \\ & C_{b} = 30 \; pF, \; R_{b} = 2.7 \; k\Omega \end{split}$	38		ns
		$\label{eq:2.4} \begin{split} & 2.4 \; V \leq EV_{DD0} < 3.3 \; V, \\ & 1.6 \; V \leq V_b \leq 2.0 \; V, \\ & C_b = 30 \; pF, \; R_b = 5.5 \; k\Omega \end{split}$	38		ns
Delay time from SCKp↓ to SOp output ^{Note}	tkso1			200	ns
		$\label{eq:VDD0} \begin{split} & 2.7 \; V \leq EV_{DD0} < 4.0 \; V, \\ & 2.3 \; V \leq V_{b} \leq 2.7 \; V, \\ & C_{b} = 30 \; pF, \; R_{b} = 2.7 \; k\Omega \end{split}$		390	ns
		$\label{eq:VDD0} \begin{array}{l} 2.4 \ V \leq EV_{DD0} < 3.3 \ V, \\ 1.6 \ V \leq V_b \leq 2.0 \ V, \\ C_b = 30 \ pF, \ R_b = 5.5 \ k\Omega \end{array}$		966	ns

Note When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1.

(Remarks are listed on the page after the next page.)



Caution Select the TTL input buffer for the SIp pin and the N-ch open drain output (VDD tolerance (for the 30- to 52-pin products)/EVDD tolerance (for the 64- to 100-pin products)) mode for the SOp pin and SCKp pin by using port input mode register g (PIMg) and port output mode register g (POMg). For VIH and VIL, see the DC characteristics with TTL input buffer selected.

(7) Communication at different potential (1.8 V, 2.5 V, 3 V) (CSI mode) (slave mode, SCKp... external clock input)

1	$x = -40$ to +105°C, 2.4 V \leq EVDD0 = EVDD1 \leq VDD \leq 5.5 V, Vss = EVss0 = EVss1 = 0	0 V)
	$(-40 10 + 103 C, 2.4 V \le LVDD0 - LVDD1 \le VDD \le 3.3 V, V33 - LV330 - LV331 - 0$	J V J

Parameter	Symbol	Conditions		HS (high-spee	ed main) mode	Unit
			MIN.	MAX.		
SCKp cycle time Note 1	tксү2	$\begin{array}{l} 4.0 \ V \leq E V_{DD0} \leq 5.5 \ V, \\ 2.7 \ V \leq V_b \leq 4.0 \ V \end{array}$	24 MHz < fмск	28/f мск		ns
			$20 \text{ MHz} < f_{\text{MCK}} \leq 24 \text{ MHz}$	24/fмск		ns
			$8 \text{ MHz} < \text{fmck} \le 20 \text{ MHz}$	20/fмск		ns
			$4 \text{ MHz} < f_{\text{MCK}} \le 8 \text{ MHz}$	16/fмск		ns
			fмск ≤ 4 MHz	12/fмск		ns
		$2.7 \text{ V} \leq \text{EV}_{\text{DD0}} < 4.0 \text{ V},$	24 MHz < fмск	40/fмск		ns
		$2.3~V \leq V_b \leq 2.7~V$	$20 \text{ MHz} < f_{\text{MCK}} \leq 24 \text{ MHz}$	32/fмск		ns
			$16 \text{ MHz} < f_{\text{MCK}} \le 20 \text{ MHz}$	28/fмск		ns
			8 MHz < fmck \leq 16 MHz	24/fмск		ns
			$4 \text{ MHz} < \text{fmck} \le 8 \text{ MHz}$	16/fмск		ns
			fмск ≤ 4 MHz	12/fмск		ns
		$2.4 \text{ V} \leq \text{EV}_{\text{DD0}} < 3.3 \text{ V},$	24 MHz < fмск	96/fмск		ns
		$1.6~V \leq V_b \leq 2.0~V$	$20 \text{ MHz} < \text{fmck} \le 24 \text{ MHz}$	72/fмск		ns
			$16 \text{ MHz} < f_{\text{MCK}} \le 20 \text{ MHz}$	64/fмск		ns
			8 MHz < fmck \leq 16 MHz	52/f мск		ns
			$4 \text{ MHz} < \text{fmck} \le 8 \text{ MHz}$	32/fмск		ns
			fмск ≤ 4 MHz	20/fмск		ns
SCKp high-/low-level	tĸн₂, tĸ∟₂	$4.0 \text{ V} \le \text{EV}_{\text{DD0}} \le 5.5 \text{ V}, 2.$	$7 \text{ V} \leq \text{V}_b \leq 4.0 \text{ V}$	tĸcy2/2 - 24		ns
width		$2.7 \text{ V} \le \text{EV}_{\text{DD0}} < 4.0 \text{ V}, 2.10 \text{ V}$	$3 \text{ V} \leq \text{V}_b \leq 2.7 \text{ V}$	tkcy2/2 - 36		ns
		$2.4 \text{ V} \le \text{EV}_{\text{DD0}} < 3.3 \text{ V}, 1.$	$6 \text{ V} \leq \text{V}_b \leq 2.0 \text{ V}$	tксү2/2 - 100		ns
SIp setup time	tsıĸ2	$4.0 \text{ V} \leq \text{EV}_{\text{DD0}} \leq 5.5 \text{ V}, 2.$	$7~V \leq V_b \leq 4.0~V$	1/fмск + 40		ns
(to SCKp↑) Note 2		$2.7 \text{ V} \le \text{EV}_{\text{DD0}} < 4.0 \text{ V}, 2.10 \text{ V}$	$3 \text{ V} \leq \text{V}_b \leq 2.7 \text{ V}$	1/fмск + 40		ns
		$2.4 \text{ V} \le \text{EV}_{\text{DD0}} < 3.3 \text{ V}, 1.$	$6 \text{ V} \leq \text{V}_b \leq 2.0 \text{ V}$	1/fмск + 60		ns
SIp hold time (from SCKp↑) ^{Note 3}	tksi2			1/fмск + 62		ns
Delay time from SCKp↓ to SOp output ^{Note 4}	tĸso2	$\begin{array}{l} 4.0 \; V \leq EV_{DD0} \leq 5.5 \; V, 2.7 \; V \leq V_b \leq 4.0 \; V, \\ C_b = 30 \; pF, \; R_b = 1.4 \; k\Omega \end{array}$			2/fмск + 240	ns
		$\begin{array}{l} 2.7 \; V \leq E V_{DD0} < 4.0 \; V, 2.3 \; V \leq V_b \leq 2.7 \; V, \\ C_b = 30 \; pF, \; R_b = 2.7 \; k\Omega \end{array}$			2/fмск + 428	ns
		$2.4 \text{ V} \leq \text{EV}_{\text{DD0}} < 3.3 \text{ V}, 1.$ Cb = 30 pF, Rv = 5.5 k Ω	$6 \text{ V} \leq \text{V}_b \leq 2.0 \text{ V},$		2/fмск + 1146	ns

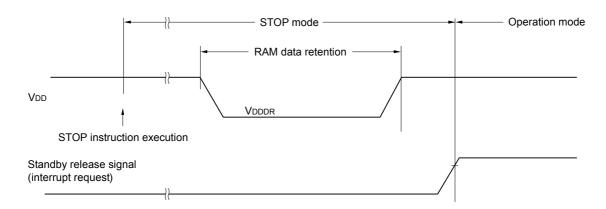
(Notes, Caution, and Remarks are listed on the next page.)



3.7 **RAM Data Retention Characteristics**

(TA = -40 to +105°C, Vss = 0V)						
Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
Data retention supply voltage	VDDDR		1.44 Note		5.5	V

Note The value depends on the POR detection voltage. When the voltage drops, the RAM data is retained before a POR reset is effected, but RAM data is not retained when a POR reset is effected.



3.8 **Flash Memory Programming Characteristics**

(T _A = -40 to +105°C	$V_{\rm r}, 2.4 \ V \le V \text{DD} \le 5.5 \ V, \ V \text{ss} = 0 \ V$	
	,	

Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
System clock frequency	fclk	$2.4 \text{ V} \leq \text{V}_{DD} \leq 5.5 \text{ V}$	1		32	MHz
Number of code flash rewrites Notes 1, 2, 3	Cerwr	Retained for 20 years TA = 85°C ^{Note 4}	1,000			Times
Number of data flash rewrites Notes 1, 2, 3		Retained for 1 year TA = 25°C		1,000,000		
		Retained for 5 years TA = 85°C ^{Note 4}	100,000			
		Retained for 20 years T _A = 85°C ^{Note 4}	10,000			

Note 1. 1 erase + 1 write after the erase is regarded as 1 rewrite. The retaining years are until next rewrite after the rewrite.

Note 2. When using flash memory programmer and Renesas Electronics self-programming library

Note 3. These are the characteristics of the flash memory and the results obtained from reliability testing by Renesas Electronics Corporation.

Note 4. This temperature is the average value at which data are retained.

3.9 Dedicated Flash Memory Programmer Communication (UART)

(TA = -40 to +105°C, 2.4 V \leq EVDD0 = EVDD1 \leq VDD \leq 5.5 V, Vss = EVss0 = EVss1 = 0 V)

Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
Transfer rate		During serial programming	115,200		1,000,000	bps



R5F104PKAFB, R5F104PLAFB R5F104PKGFB, R5F104PLGFB

